

Michael J Manfra

List of Publications by Year in descending order

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178
papers

6,757
citations

66234

42
h-index

74018

75
g-index

178
all docs

178
docs citations

178
times ranked

5665
citing authors

#	ARTICLE	IF	CITATIONS
1	Scaling of Majorana Zero-Bias Conductance Peaks. Physical Review Letters, 2017, 119, 136803.	2.9	338
2	Direct imaging of reverse-bias leakage through pure screw dislocations in GaN films grown by molecular beam epitaxy on GaN templates. Applied Physics Letters, 2002, 81, 79-81.	1.5	283
3	Inhomogeneous spatial distribution of reverse bias leakage in GaN Schottky diodes. Applied Physics Letters, 2001, 78, 1685-1687.	1.5	279
4	Evidence of topological superconductivity in planar Josephson junctions. Nature, 2019, 569, 89-92.	13.7	261
5	Direct observation of anyonic braiding statistics. Nature Physics, 2020, 16, 931-936.	6.5	217
6	Noise Suppression Using Symmetric Exchange Gates in Spin Qubits. Physical Review Letters, 2016, 116, 116801.	2.9	186
7	High-fidelity entangling gate for double-quantum-dot spin qubits. Npj Quantum Information, 2017, 3, .	2.8	174
8	Poole-Frenkel electron emission from the traps in AlGaIn/GaN transistors. Journal of Applied Physics, 2004, 95, 6414-6419.	1.1	169
9	Collective non-perturbative coupling of 2D electrons with high-quality-factor terahertz cavity photons. Nature Physics, 2016, 12, 1005-1011.	6.5	166
10	Superconducting gatemon qubit based on a proximitized two-dimensional electron gas. Nature Nanotechnology, 2018, 13, 915-919.	15.6	138
11	Supercurrent rectification and magnetochiral effects in symmetric Josephson junctions. Nature Nanotechnology, 2022, 17, 39-44.	15.6	134
12	Effect of growth stoichiometry on the electrical activity of screw dislocations in GaN films grown by molecular-beam epitaxy. Applied Physics Letters, 2001, 78, 3980-3982.	1.5	116
13	Mechanisms of gate lag in GaN/AlGaIn/GaN high electron mobility transistors. Superlattices and Microstructures, 2003, 34, 33-53.	1.4	114
14	Nonconventional Odd-Denominator Fractional Quantum Hall States in the Second Landau Level. Physical Review Letters, 2010, 105, 246808.	2.9	112
15	Topological superconductivity in hybrid devices. Nature Physics, 2020, 16, 718-724.	6.5	105
16	A cryogenic CMOS chip for generating control signals for multiple qubits. Nature Electronics, 2021, 4, 64-70.	13.1	105
17	High-mobility AlGaIn/GaN heterostructures grown by molecular-beam epitaxy on GaN templates prepared by hydride vapor phase epitaxy. Applied Physics Letters, 2000, 77, 2888-2890.	1.5	99
18	Vacuum Bloch-Siegert shift in Landau polaritons with ultra-high cooperativity. Nature Photonics, 2018, 12, 324-329.	15.6	98

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19	Molecular Beam Epitaxy of Ultra-High-Quality AlGaAs/GaAs Heterostructures: Enabling Physics in Low-Dimensional Electronic Systems. Annual Review of Condensed Matter Physics, 2014, 5, 347-373.	5.2	97
20	Induced superconductivity in high-mobility two-dimensional electron gas in gallium arsenide heterostructures. Nature Communications, 2015, 6, 7426.	5.8	97
21	Superradiant Decay of Cyclotron Resonance of Two-Dimensional Electron Gases. Physical Review Letters, 2014, 113, 047601.	2.9	88
22	Electric and Magnetic Tuning Between the Trivial and Topological Phases in InAs/GaSb Double Quantum Wells. Physical Review Letters, 2015, 115, 036803.	2.9	82
23	Notch filtering the nuclear environment of a spin qubit. Nature Nanotechnology, 2017, 12, 16-20.	15.6	80
24	Acoustic phonon scattering in a low density, high mobility AlGaIn/GaN field-effect transistor. Applied Physics Letters, 2005, 86, 252108.	1.5	75
25	High mobility AlGaIn/GaN heterostructures grown by plasma-assisted molecular beam epitaxy on semi-insulating GaN templates prepared by hydride vapor phase epitaxy. Journal of Applied Physics, 2002, 92, 338-345.	1.1	73
26	Aharonov-Bohm interference of fractional quantum Hall edge modes. Nature Physics, 2019, 15, 563-569.	6.5	72
27	Coherent spin-state transfer via Heisenberg exchange. Nature, 2019, 573, 553-557.	13.7	71
28	Observation of a transition from a topologically ordered to a spontaneously broken symmetry phase. Nature Physics, 2016, 12, 191-195.	6.5	68
29	Spectrum of the Nuclear Environment for GaAs Spin Qubits. Physical Review Letters, 2017, 118, 177702.	2.9	67
30	Transport and Percolation in a Low-Density High-Mobility Two-Dimensional Hole System. Physical Review Letters, 2007, 99, 236402.	2.9	63
31	Impact of Si doping on radio frequency dispersion in unpassivated GaN/AlGaIn/GaN high-electron-mobility transistors grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2003, 82, 4361-4363.	1.5	57
32	Electron mobility exceeding $160000\text{cm}^2/\text{Vs}$ in AlGaIn/GaN heterostructures grown by molecular-beam epitaxy. Applied Physics Letters, 2004, 85, 5394-5396.	1.5	57
33	Repeatable low-temperature negative-differential resistance from Al _{0.18} Ga _{0.82} N/GaN resonant tunneling diodes grown by molecular-beam epitaxy on free-standing GaN substrates. Applied Physics Letters, 2012, 100, .	1.5	56
34	Relating Andreev Bound States and Supercurrents in Hybrid Josephson Junctions. Physical Review Letters, 2020, 124, 226801.	2.9	53
35	Direct entropy measurement in a mesoscopic quantum system. Nature Physics, 2018, 14, 1083-1086.	6.5	52
36	Effect of Strain on Stripe Phases in the Quantum Hall Regime. Physical Review Letters, 2011, 106, 016804.	2.9	50

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37	Modified MBE hardware and techniques and role of gallium purity for attainment of two dimensional electron gas mobility $\gt;35\text{\AA}-106\text{cm}^2/\text{V s}$ in AlGaAs/GaAs quantum wells grown by MBE. Journal of Crystal Growth, 2016, 441, 71-77.	0.7	50
38	Dynamics of trapped charge in GaN/AlGaIn/GaN high electron mobility transistors grown by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2004, 84, 422-424.	1.5	49
39	Quantized Conductance and Large $\langle i \rangle g \langle /i \rangle$ -Factor Anisotropy in InSb Quantum Point Contacts. Nano Letters, 2016, 16, 7509-7513.	4.5	49
40	Observation of Dirac bands in artificial graphene in small-period nanopatterned GaAs quantum wells. Nature Nanotechnology, 2018, 13, 29-33.	15.6	49
41	High mobility two-dimensional hole system in GaAs $\hat{\cdot}$ AlGaAs quantum wells grown on (100) GaAs substrates. Applied Physics Letters, 2005, 86, 162106.	1.5	45
42	Electron mobility in very low density GaN $\hat{\cdot}$ AlGaIn $\hat{\cdot}$ GaN heterostructures. Applied Physics Letters, 2004, 85, 1722-1724.	1.5	43
43	Electron scattering in AlGaIn/GaN structures. Applied Physics Letters, 2004, 84, 1507-1509.	1.5	42
44	Contrasting energy scales of reentrant integer quantum Hall states. Physical Review B, 2012, 86, .	1.1	42
45	Hydrodynamic and Ballistic Transport over Large Length Scales in $\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mi} \rangle \text{GaAs} \langle \text{mml:mi} \rangle \langle \text{mml:mo} \rangle \langle \text{mml:mi} \rangle \text{AlGaAs} \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle$ Physical Review Letters, 2021, 126, 076803.	2.9	42
46	Ballistic superconductivity and tunable $\hat{\text{I}}\hat{\text{C}}\hat{\text{I}}$ junctions in InSb quantum wells. Nature Communications, 2019, 10, 3764.	5.8	40
47	Full control of quadruple quantum dot circuit charge states in the single electron regime. Applied Physics Letters, 2014, 104, .	1.5	39
48	Coherent transport through a Majorana island in an Aharonov $\hat{\text{I}}$ Bohm interferometer. Nature Communications, 2020, 11, 3212.	5.8	39
49	Effect of Rashba and Dresselhaus spin $\hat{\text{I}}$ orbit coupling on supercurrent rectification and magnetochiral anisotropy of ballistic Josephson junctions. Journal of Physics Condensed Matter, 2022, 34, 154005.	0.7	39
50	Quantitative analysis of the disorder broadening and the intrinsic gap for the $\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mi} \rangle \hat{1}/2 \langle \text{mml:mi} \rangle \langle \text{mml:mo} \rangle = \langle \text{mml:mo} \rangle \langle \text{mml:mfrac} \rangle \langle \text{mml:mn} \rangle 5 \langle \text{mml:mn} \rangle \langle \text{mml:mn} \rangle 2 \langle \text{mml:mn} \rangle$ quantum Hall state. Physical Review B, 2011, 84, .	1.1	38
51	Decoupling Edge Versus Bulk Conductance in the Trivial Regime of an $\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mi} \rangle \text{InAs} \langle \text{mml:mi} \rangle \langle \text{mml:mo} \rangle \langle \text{mml:mi} \rangle \text{GaSb} \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle$ Quantum Well Using Corbino Ring Geometry. Physical Review Letters, 2016, 117, 077701.	2.9	38
52	Fast spin exchange across a multielectron mediator. Nature Communications, 2019, 10, 1196.	5.8	37
53	Nonparabolicity of the conduction band of wurtzite GaN. Applied Physics Letters, 2003, 83, 4553-4555.	1.5	36
54	Dislocation and morphology control during molecular-beam epitaxy of AlGaIn/GaN heterostructures directly on sapphire substrates. Applied Physics Letters, 2002, 81, 1456-1458.	1.5	35

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55	High-reflectivity ultraviolet AlGaIn ^x AlGaIn distributed Bragg reflectors. Applied Physics Letters, 2006, 88, 171101.	1.5	35
56	Evidence for effective mass reduction in GaAs/AlGaAs quantum wells. Physical Review B, 2013, 87, .	1.1	34
57	Symmetric operation of the resonant exchange qubit. Physical Review B, 2017, 96, .	1.1	34
58	Hybridization of Subgap States in One-Dimensional Superconductor-Semiconductor Coulomb Islands. Physical Review Letters, 2018, 121, 256803.	2.9	34
59	Adiabatic quantum state transfer in a semiconductor quantum-dot spin chain. Nature Communications, 2021, 12, 2156.	5.8	34
60	Giant Spin-Orbit Splitting in Inverted Quantum Wells. Physical Review Letters, 2017, 118, 016801.	2.9	33
61	Superconducting Quantum Interference through Trivial Edge States in InAs. Physical Review Letters, 2018, 120, 047702.	2.9	33
62	Near-infrared intersubband absorption in molecular-beam epitaxy-grown lattice-matched InAlN/GaN superlattices. Applied Physics Letters, 2009, 94, 161111.	1.5	31
63	Spin-orbit interaction in a dual gated InAs/GaSb quantum well. Physical Review B, 2017, 96, .	1.1	31
64	III-V gate-all-around nanowire MOSFET process technology: From 3D to 4D. , 2012, , .		30
65	Quantum Hall State in the Presence of Alloy Disorder. Physical Review Letters, 2014, 112, 116804.	2.9	30
66	Quantum and transport lifetimes in a tunable low-density AlGaIn ^x GaN two-dimensional electron gas. Applied Physics Letters, 2004, 85, 5278-5280.	1.5	29
67	Improvement of near-infrared absorption linewidth in AlGaIn/GaN superlattices by optimization of delta-doping location. Applied Physics Letters, 2012, 101, .	1.5	29
68	Gate-tunable high mobility remote-doped InSb/In ^{1-x} Al ^x Sb quantum well heterostructures. Applied Physics Letters, 2015, 106, .	1.5	29
69	Comparative study of intersubband absorption in AlGaIn/GaN and AlInN/GaN superlattices: Impact of material inhomogeneities. Physical Review B, 2013, 88, .	1.1	28
70	Negative Spin Exchange in a Multielectron Quantum Dot. Physical Review Letters, 2017, 119, 227701.	2.9	26
71	Spin of a Multielectron Quantum Dot and Its Interaction with a Neighboring Electron. Physical Review X, 2018, 8, .	2.8	26
72	High-mobility InAs 2DEGs on GaSb substrates: A platform for mesoscopic quantum transport. Physical Review Materials, 2018, 2, .	0.9	26

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91	Near-Infrared Absorption in Lattice-Matched AlInN/GaN and Strained AlGaIn/GaN Heterostructures Grown by MBE on Low-Defect GaN Substrates. <i>Journal of Electronic Materials</i> , 2012, 41, 881-886.	1.0	19
92	Evidence for a new symmetry breaking mechanism reorienting quantum Hall nematics. <i>Physical Review B</i> , 2016, 93, .	1.1	18
93	Long-Distance Superexchange between Semiconductor Quantum-Dot Electron Spins. <i>Physical Review Letters</i> , 2021, 126, 017701.	2.9	18
94	Cyclotron mass of two-dimensional holes in (100) oriented GaAs $\hat{\wedge}$ AlGaAs heterostructures. <i>Applied Physics Letters</i> , 2008, 92, 012109.	1.5	17
95	Surface morphology and electronic properties of dislocations in AlGaIn/GaN heterostructures. <i>Journal of Electronic Materials</i> , 2001, 30, 110-114.	1.0	16
96	Exploration of the limits to mobility in two-dimensional hole systems in GaAs/AlGaAs quantum wells. <i>Physical Review B</i> , 2012, 85, .	1.1	16
97	Low-temperature illumination and annealing of ultrahigh quality quantum wells. <i>Physical Review B</i> , 2014, 90, .	1.1	16
98	Microwave-induced resistance oscillations in a back-gated GaAs quantum well. <i>Physical Review B</i> , 2017, 95, .	1.1	16
99	Quantum transport in high mobility AlGaIn/GaN 2DEGs and nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1706-1712.	0.7	15
100	Scattering mechanisms in a high-mobility low-density carbon-doped (100) GaAs two-dimensional hole system. <i>Physical Review B</i> , 2011, 83, .	1.1	15
101	Onset of quantum criticality in the topological-to-nematic transition in a two-dimensional electron gas at filling factor $\nu=5/2$. <i>Physical Review B</i> , 2017, 96, .	1.1	15
102	Floquet-enhanced spin swaps. <i>Nature Communications</i> , 2021, 12, 2142.	5.8	15
103	In-surface confinement of topological insulator nanowire surface states. <i>Applied Physics Letters</i> , 2015, 107, 121605.	1.5	14
104	Topological kink plasmons on magnetic-domain boundaries. <i>Nature Communications</i> , 2019, 10, 4565.	5.8	14
105	Impact of growth conditions and strain on indium incorporation in non-polar m-plane (101 $\hat{\wedge}$) InGaIn grown by plasma-assisted molecular beam epitaxy. <i>APL Materials</i> , 2019, 7, .	2.2	14
106	Josephson Inductance as a Probe for Highly Ballistic Semiconductor-Superconductor Weak Links. <i>Physical Review Letters</i> , 2021, 126, 037001.	2.9	14
107	Growth and electrical characterization of Al _{0.24} Ga _{0.76} As/Al _x Ga _{1-x} As/Al _{0.24} Ga _{0.76} As modulation-doped quantum wells with extremely low x. <i>Applied Physics Letters</i> , 2013, 102, 252103.	1.5	13
108	Electron bubbles and the structure of the orbital wave function. <i>Physical Review B</i> , 2019, 99, .	1.1	13

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109	Band Structure Extraction at Hybrid Narrow-Gap Semiconductor-Metal Interfaces. <i>Advanced Science</i> , 2021, 8, 2003087.	5.6	13
110	Magnetoplasmon resonance in a two-dimensional electron system driven into a zero-resistance state. <i>Physical Review B</i> , 2012, 85, .	1.1	12
111	Transport of a sliding Wigner crystal in the four flux composite fermion regime. <i>Physical Review B</i> , 2015, 92, .	1.1	12
112	Stability of High-Density Two-Dimensional Excitons against a Mott Transition in High Magnetic Fields Probed by Coherent Terahertz Spectroscopy. <i>Physical Review Letters</i> , 2016, 117, 207402.	2.9	12
113	Quantum Dots in an $\ln\text{Sb}$ Two-Dimensional Electron Gas. <i>Physical Review Applied</i> , 2020, 13, .	1.5	12
114	Shubnikov-de Haas oscillations in a two-dimensional electron gas under subterahertz radiation. <i>Physical Review B</i> , 2015, 92, .	1.1	11
115	Gapped excitations of unconventional fractional quantum Hall effect states in the second Landau level. <i>Physical Review B</i> , 2015, 92, .	1.1	11
116	Optical Emission Spectroscopy Study of Competing Phases of Electrons in the Second Landau Level. <i>Physical Review Letters</i> , 2016, 116, 016801.	2.9	11
117	Effect of density on quantum Hall stripe orientation in tilted magnetic fields. <i>Physical Review B</i> , 2017, 95, .	1.1	11
118	Kinetic instability of AlGaIn alloys during MBE growth under metal-rich conditions on m-plane GaN miscut towards the -c axis. <i>Journal of Applied Physics</i> , 2018, 123, 161581.	1.1	11
119	Gate-defined quantum point contact in an InAs two-dimensional electron gas. <i>Physical Review B</i> , 2019, 100, .	1.1	11
120	Repairing the surface of InAs-based topological heterostructures. <i>Journal of Applied Physics</i> , 2020, 128, 114301.	1.1	11
121	Zeeman-driven parity transitions in an Andreev quantum dot. <i>Physical Review B</i> , 2021, 103, .	1.1	11
122	Impact of bulk-edge coupling on observation of anyonic braiding statistics in quantum Hall interferometers. <i>Nature Communications</i> , 2022, 13, 344.	5.8	11
123	Magnetotransport in Zener tunneling regime in a high-mobility two-dimensional hole gas. <i>Physical Review B</i> , 2009, 80, .	1.1	10
124	Observation of electron states of small period artificial graphene in nano-patterned GaAs quantum wells. <i>Applied Physics Letters</i> , 2016, 109, 113101.	1.5	10
125	Optimization of edge state velocity in the integer quantum Hall regime. <i>Physical Review B</i> , 2018, 97, .	1.1	10
126	A Robust Protocol for Entropy Measurement in Mesoscopic Circuits. <i>Entropy</i> , 2022, 24, 417.	1.1	10

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127	Electron-Hole Asymmetric Chiral Breakdown of Reentrant Quantum Hall States. <i>Physical Review Letters</i> , 2016, 117, 166805.	2.9	9
128	Photoluminescence study of non-polar m-plane InGaN and nearly strain-balanced InGaN/AlGaN superlattices. <i>Journal of Applied Physics</i> , 2020, 127, .	1.1	9
129	Effect of dislocations on local transconductance in AlGaN/GaN heterostructures as imaged by scanning gate microscopy. <i>Applied Physics Letters</i> , 2003, 83, 4559-4561.	1.5	8
130	Dramatic enhancement of near-infrared intersubband absorption in c-plane AlInN/GaN superlattices. <i>Applied Physics Letters</i> , 2016, 108, .	1.5	8
131	Anomalous Nematic States in High Half-Filled Landau Levels. <i>Physical Review Letters</i> , 2020, 124, 067601.	2.9	8
132	Anodic oxidation of epitaxial superconductor-semiconductor hybrids. <i>Physical Review Materials</i> , 2021, 5, .	0.9	8
133	Particle-hole asymmetry of fractional quantum Hall states in the second Landau level of a two-dimensional hole system. <i>Physical Review B</i> , 2011, 83, .	1.1	7
134	Field-effect-induced two-dimensional electron gas utilizing modulation-doped ohmic contacts. <i>Solid State Communications</i> , 2014, 197, 20-24.	0.9	7
135	Multiphoton processes at cyclotron resonance subharmonics in a two-dimensional electron system under dc and microwave excitation. <i>Physical Review B</i> , 2014, 90, .	1.1	7
136	Apparent temperature-induced reorientation of quantum Hall stripes. <i>Physical Review B</i> , 2017, 95, .	1.1	7
137	Effect of illumination on quantum lifetime in GaAs quantum wells. <i>Physical Review B</i> , 2018, 98, .	1.1	7
138	Intersubband Transitions in Nonpolar m -Plane AlGaN/GaN Heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700828.	0.8	7
139	Observation of new plasmons in the fractional quantum Hall effect: Interplay of topological and nematic orders. <i>Science Advances</i> , 2019, 5, eaav3407.	4.7	7
140	Indium surfactant assisted epitaxy of non-polar ($101\hat{A}^{-0}$) AlGaN/InGaN multiple quantum well heterostructures. <i>Journal of Applied Physics</i> , 2020, 128, 115701.	1.1	7
141	Observation of Flat Bands in Gated Semiconductor Artificial Graphene. <i>Physical Review Letters</i> , 2021, 126, 106402.	2.9	7
142	Toward durable Al-InSb hybrid heterostructures via epitaxy of 2ML interfacial InAs screening layers. <i>Physical Review Materials</i> , 2019, 3, .	0.9	7
143	Mesoscopic structures and two-dimensional hole systems in fully field effect controlled heterostructures. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	6
144	Resistively detected high-order magnetoplasmons in a high-quality two-dimensional electron gas. <i>Physical Review B</i> , 2016, 93, .	1.1	6

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145	High-temperature resistivity measured at $\nu = \frac{1}{2}$ as a predictor of the two-dimensional electron gas quality in the Landau level. <i>Physical Review B</i> , 2017, 95, .	1.1	6
146	Precision measurement of electron-electron scattering in GaAs/AlGaAs using transverse magnetic focusing. <i>Nature Communications</i> , 2021, 12, 5048.	5.8	6
147	High power GaN/AlGaN/GaN HEMTs operating at 2 to 25 GHz grown by plasma-assisted MBE. <i>Physica Status Solidi A</i> , 2003, 200, 175-178.	1.7	5
148	Few-Electron Single and Double Quantum Dots in an InAs Two-Dimensional Electron Gas. <i>PRX Quantum</i> , 2021, 2, .	3.5	5
149	Free standing GaN nano membrane by laser lift-off method. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1432, 53.	0.1	4
150	Integrated high electron mobility transistors in GaAs/AlGaAs heterostructures for amplification at sub-Kelvin temperatures. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	4
151	Resistivity anisotropy of quantum Hall stripe phases. <i>Physical Review B</i> , 2019, 100, .	1.1	4
152	Reduction of charge noise in shallow GaAs/AlGaAs heterostructures with insulated gates. <i>Applied Physics Letters</i> , 2020, 117, 133504.	1.5	4
153	Stability of multielectron bubbles in high Landau levels. <i>Physical Review B</i> , 2020, 102, .	1.1	4
154	Mid-infrared intersubband absorption in strain-balanced non-polar (In)AlGaN/InGaN multi-quantum wells. <i>Optical Materials Express</i> , 2021, 11, 3284.	1.6	4
155	Measurements of cyclotron resonance of the interfacial states in strong spin-orbit coupled 2D electron gases proximitized with aluminum. <i>Applied Physics Letters</i> , 2022, 120, 142105.	1.5	4
156	Millimeter wave transmission spectroscopy of gated two-dimensional hole systems. <i>Applied Physics Letters</i> , 2012, 100, 192104.	1.5	3
157	Observation of Photoinduced Terahertz Gain in GaAs Quantum Wells: Evidence for Radiative Two-Exciton-to-Biexciton Scattering. <i>Physical Review Letters</i> , 2020, 125, 167401.	2.9	3
158	Disorder broadening of even-denominator fractional quantum Hall states in the presence of a short-range alloy potential. <i>Physical Review B</i> , 2020, 102, .	1.1	3
159	LARGE CYCLOTRON-RESONANCE LINE SPLITTING OF TWO-DIMENSIONAL ELECTRONS IN AlGaN/GaN AND AlGaAs/GaAs HETEROSTRUCTURES. <i>International Journal of Modern Physics B</i> , 2004, 18, 3761-3768.	1.0	2
160	Strong heavy-to-light hole intersubband absorption in the valence band of carbon-doped GaAs/AlAs superlattices. <i>Journal of Applied Physics</i> , 2013, 113, 053103.	1.1	2
161	Impact of short-range scattering on the metallic transport of strongly correlated two-dimensional holes in GaAs quantum wells. <i>Physical Review B</i> , 2014, 90, .	1.1	2
162	Overcoming anomalous suppression of m-plane AlGaN growth by molecular-beam epitaxy using indium as a surfactant. <i>Journal of Applied Physics</i> , 2021, 130, 105702.	1.1	2

